

BD533 BD535 BD537 BD534 BD536

Complementary power transistors

Features

■ BD533, BD535, and BD537 are NPN transistors

Description

The devices are manufactured in Planar technology with "Base Island" layout. The resulting transistor shows exceptional high gain performance coupled with very low saturation voltage. The PNP types are BD534 and BD536.

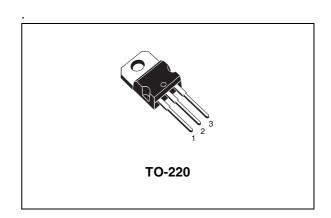


Figure 1. Internal schematic diagrams

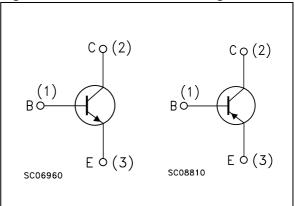


Table 1. Device summary

| Order code | Marking | Package | Packaging |
|------------|---------|---------|-----------|
| BD533 | BD533 | | |
| BD534 | BD534 | | |
| BD535 | BD535 | TO-220 | Tube |
| BD536 | BD536 | | |
| BD537 | BD537 | | |

1 Absolute maximum ratings

Table 2. Absolute maximum ratings

| Symbol | Parameter | | Value | | | Unit |
|------------------|--|-----|------------|-------|-------|------|
| | | NPN | BD533 | BD535 | BD537 | |
| | | PNP | BD534 | BD536 | | |
| V _{CBO} | Collector-base voltage (I _E = 0) | | 45 | 60 | 80 | V |
| V _{CES} | Collector-emitter voltage (V _B = 0) | | 45 | 60 | 80 | V |
| V _{CEO} | Collector-base voltage (I _B = 0) | | 45 | 60 | 80 | ٧ |
| V _{EBO} | Emitter-base voltage (I _C = 0) | | | 5 | | V |
| I _C | Collector current | | | 8 | | Α |
| Ι _Β | Base current | | | 1 | | Α |
| P _{TOT} | Total dissipation at T _{case} = 25°C | | | 50 | | W |
| T _{stg} | Storage temperature | | -65 to 150 | | | °C |
| TJ | Max. operating junction temperature | | 150 | | | °C |

Note: For PNP types voltage and current values are negative

Table 3. Electrical characteristics

 $(T_{case} = 25^{\circ}C; unless otherwise specified)$

Table 4. Electrical characteristics

| Symbol | Parameter | Test Con | ditions | Min. | Тур. | Max. | Unit |
|--------------------------------------|---|---|--------------------------|------|------|------|------|
| I _{CBO} | Collector cut-off current (I _E = 0) | V _{CB} = rated V _{CB} | 30 | | | 0.1 | mA |
| | Collector cut-off current (V _{BE} = 0) | for BD533/534 | V _{CE} = 45 V | | | 0.1 | mA |
| I _{CES} | | for BD535/536 | - | | | 0.1 | mA |
| | | for BD537 | V _{CE} = 80 V | | | 0.1 | mA |
| I _{EBO} | Emitter cut-off current (I _C = 0) | V _{EB} = 5V | | | | 1 | mA |
| | Collector-emitter | $I_C = 100 \text{mA}$ fo | r BD533/534 | 45 | | | ٧ |
| V _{CEO(sus)} ⁽¹⁾ | sustaining voltage | fo | r BD535/536 | 60 | | | V |
| | (I _B = 0) | fo | r BD537 | 80 | | | V |
| V (1) | Collector-emitter | $I_C = 2A$ I_E | $_{3} = 0.2A$ | | | 8.0 | V |
| V _{CE(sat)} ⁽¹⁾ | saturation voltage | $I_C = 6A$ I_E | $_{3} = 0.6A$ | | 8.0 | | V |
| V _{BE} ⁽¹⁾ | Base-emitter voltage | $I_C = 2A$ V | _{CE} = 2V | | | 1.5 | V |
| | | $I_C = 10mA$ V_C | _{CE} = 5V | | | | |
| | | fo | or BD533/534 | 20 | | | |
| | | | or BD535/536 | 20 | | | |
| (4) | | | for BD537 | 15 | | | |
| h _{FE} ⁽¹⁾ | DC current gain | $I_C = 500 \text{mA}$ V_C | | 40 | | | |
| | | $I_C = 2A$ V | _ | | | | |
| | | | or BD533/534 | 25 | | | |
| | | | or BD535/536 or BD537 | 25 | | | |
| | |] | UI BD331 | 15 | | | |

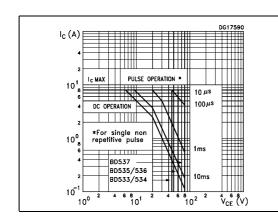
^{1.} Pulsed duration = 300 ms, duty cycle ≥1.5%.

Note: For PNP types voltage e current values are negative.

1.1 Electrical characteristic (curves)

Figure 2. Safe operating area

Figure 3. Derating curve



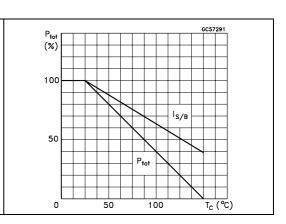
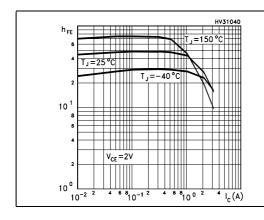


Figure 4. DC current gain (NPN)

Figure 5. DC current gain (PNP)



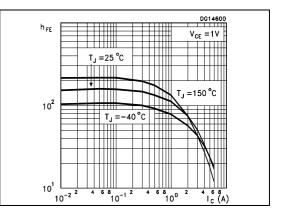
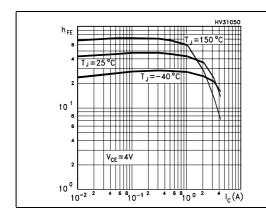


Figure 6. DC current gain (NPN)

Figure 7. DC current gain (PNP)



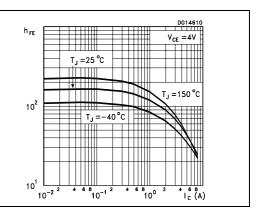
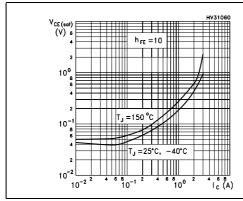


Figure 8. Collector-emitter saturation voltage (NPN)

Figure 9. Collector-emitter saturation voltage (PNP)



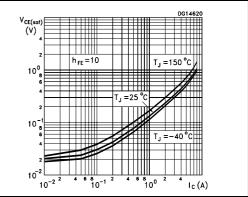
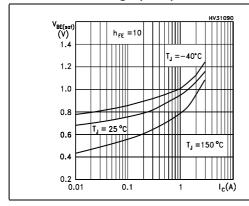


Figure 10. Base-emitter saturation voltage (NPN)

Figure 11. Base-emitter saturation voltage (PNP)



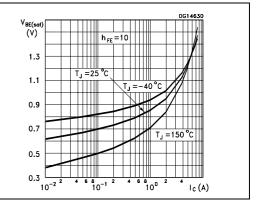
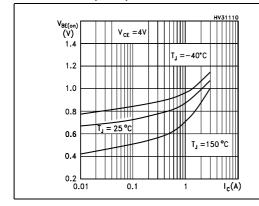


Figure 12. Base-emitter on voltage (NPN)

Figure 13. Base-emitter on voltage (PNP)



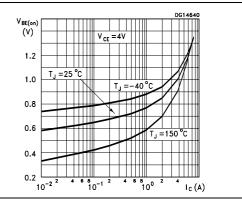


Figure 14. Resistive load switching time Figure 15. Resistive load switching time (NPN) (PNP)

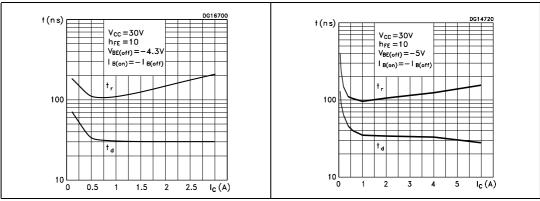


Figure 16. Resistive load switching time Figure 17. Resistive load switching time (NPN) (PNP)

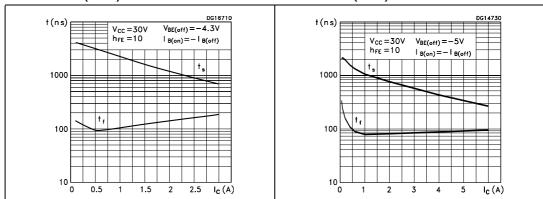
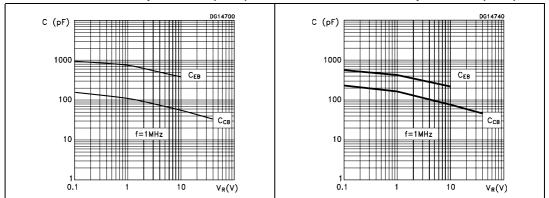


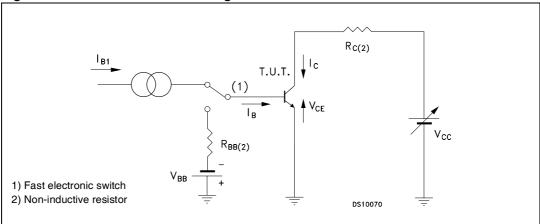
Figure 18. Collector-base and collector- Figure 19. Collector-base and collector- emitter capacitance (NPN) emitter capacitance (PNP)



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1.2 Test circuits

Figure 20. Resistive load switching test circuit

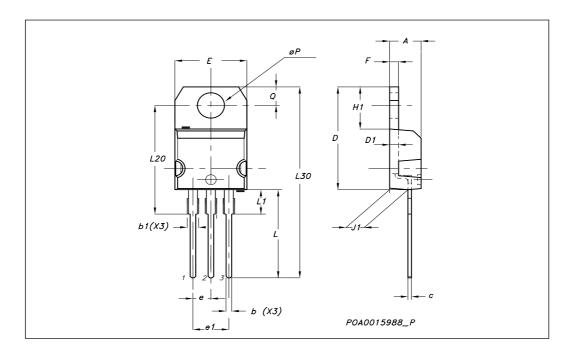


2 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

TO-220 Mechanical data

| DIM. | | mm. | | |
|------|-------|-------|-------|--|
| | MIN. | TYP | MAX. | |
| Α | 4.40 | | 4.60 | |
| b | 0.61 | | 0.88 | |
| b1 | 1.14 | | 1.70 | |
| С | 0.49 | | 0.70 | |
| D | 15.25 | | 15.75 | |
| D1 | | 1.27 | | |
| E | 10 | | 10.40 | |
| е | 2.40 | | 2.70 | |
| e1 | 4.95 | | 5.15 | |
| F | 1.23 | | 1.32 | |
| H1 | 6.20 | | 6.60 | |
| J1 | 2.40 | | 2.72 | |
| L | 13 | | 14 | |
| L1 | 3.50 | | 3.93 | |
| L20 | | 16.40 | | |
| L30 | | 28.90 | | |
| øΡ | 3.75 | | 3.85 | |
| Q | 2.65 | | 2.95 | |



3 Revision history

Table 5. Revision history

| Date | Revision | Changes |
|-------------|----------|---|
| 01-Jun-1997 | 1 | Initial Release |
| 11-Feb-2003 | 2 | Minor text changes |
| 27-Mar-2007 | 3 | Figure 4, 5, 6, 7, 8, 9, 10, 11, 12, 13, 14, 15, 16, 17, 18, 19 and figure 20 added |
| 23-Jul-2007 | 4 | Figure 2 and figure 3 added |

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